

Product Overview

NXH010P120MNF1: SiC Module, 2-PACK Half Bridge Topology, 1200 V, 10 mohm SiC MOSFET

For complete documentation, see the data sheet.

The NXH010P120MNF1 is a SiC MOSFET module containing a 10 mohm SiC MOSFET half bridge and an NTC thermistor in an F1 module.

Features

- Recommended gate voltage 18V - 20V
- Low thermal resistance
- Options for TIM or no TIM

Benefits

- Improved RDS(ON) at higher voltage
- Improved efficiency or higher power density
- Flexible solution for high reliability thermal interface

Applications

- AC-DC Conversion
- DC-AC Conversion
- DC-DC Conversion

End Products

- Electric Vehicle Charger
- Energy Storage System
- Solar Inverter 3-phase
- Uninterruptible Power Supply

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V _{BR} Max (V)	R _{DS(on)} Typ (Ω)	Package Type
NXH010P120MNF1PN G	87.9978	Pb-free Halide free non AEC- Q and PPAP	Active	2-PACK	1200	10	PIM18 33.8x42.5 (PRESS FIT)

For more information please contact your local sales support at www.onsemi.com.

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